

CentralTM Semiconductor Corp.

145 Adams Avenue, Hauppauge, NY 11788 USA
Tel: (631) 435-1110 • Fax: (631) 435-1824

Manufacturers of World Class Discrete Semiconductors

2N5366
2N5367

PNP SILICON TRANSISTOR

JEDEC TO-92 CASE (ECB)

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N5366, 2N5367 types are PNP Silicon Planar Epitaxial Transistors designed for general purpose switching and amplifier applications.

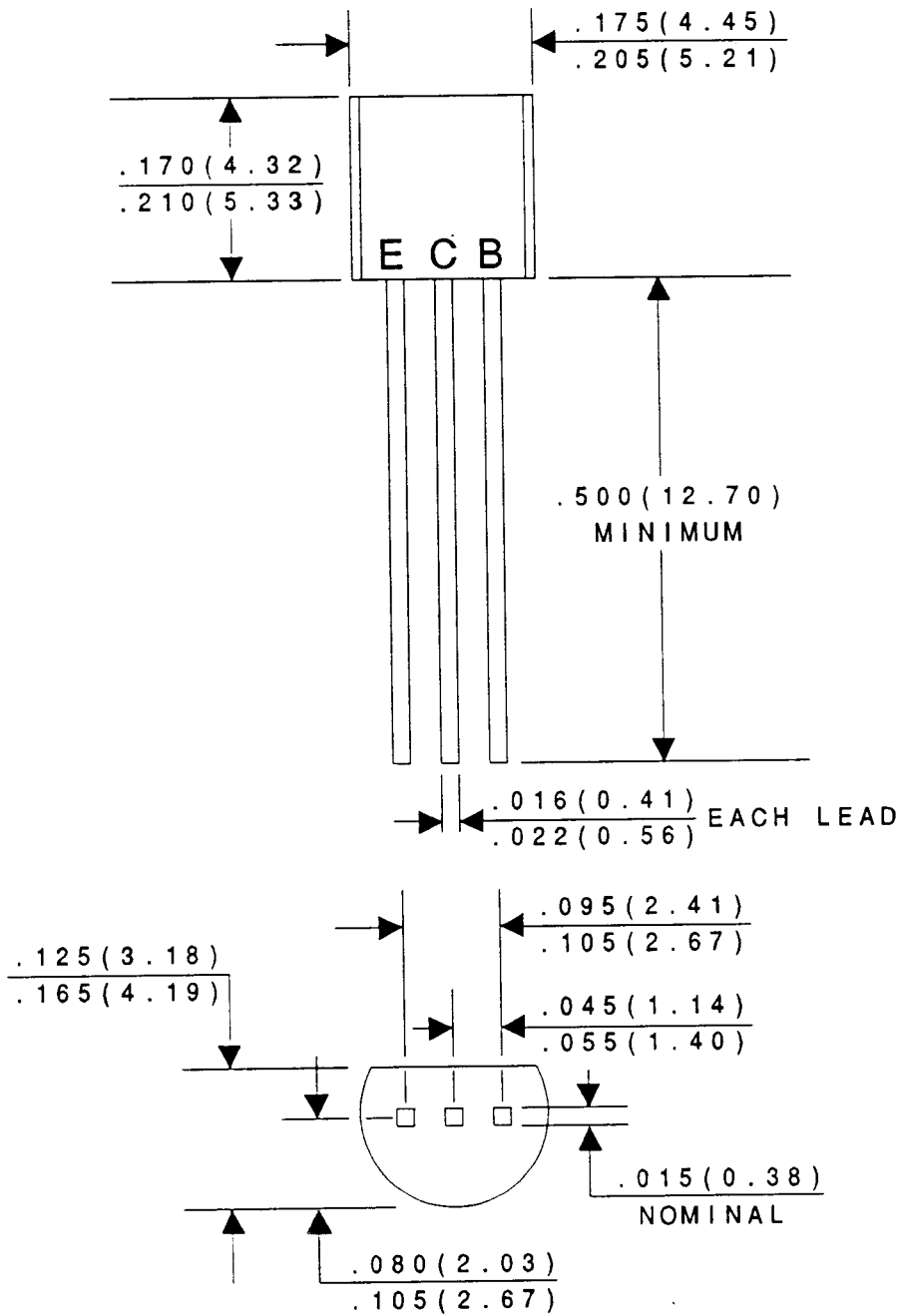
MAXIMUM RATINGS (T_A = 25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V _{CBO}	40	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	4.0	V
Continuous Collector Current	I _C	300	mA
Collector Current (t = 10μsec)	I _C	700	mA
Power Dissipation	P _D	625	mW
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	θ _{JA}	0.2	°C/mW

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	2N5366		2N5367		UNITS
		MIN	MAX	MIN	MAX	
I _{CBO}	V _{CB} = 40V		100		100	nA
I _{CBO}	V _{CB} = 40V, T _A = 100°C		10		10	μA
I _{CES}	V _{CB} = 40V		100		100	nA
I _{EBO}	V _{EB} = 4.0V		10		10	μA
BV _{CEO}	I _C = 10mA	40		40		V
V _{CE(SAT)}	I _C = 50mA, I _B = 2.5mA		0.25		0.25	V
V _{CE(SAT)}	I _C = 300mA, I _B = 30mA		1.0		1.0	V
V _{BE(SAT)}	I _C = 50mA, I _B = 2.5mA		1.1		1.1	V
V _{BE(SAT)}	I _C = 300mA, I _B = 30mA		2.0		2.0	V
V _{BE(ON)}	V _{CE} = 10V, I _C = 2.0mA	0.5	0.8	0.5	0.8	V
h _{FE}	V _{CE} = 10V, I _C = 2.0mA	80		200		
h _{FE}	V _{CE} = 1.0V, I _C = 50mA	100	300	250	500	
h _{FE}	V _{CE} = 5.0V, I _C = 300mA	40		75		
C _{ob}	V _{CB} = 10V, I _E = 0, f = 1.0MHz		8.0		8.0	pF
C _{ib}	V _{EB} = 0.5V, I _C = 0, f = 1.0MHz		35		35	pF
h _{fe}	V _{CE} = 10V, I _C = 2.0mA, f = 1.0kHz	80	450	200	750	
f _T	V _{CE} = 10V, I _C = 2.0mA		250 TYP		250 TYP	MHz

JEDEC TO-92 CASE - MECHANICAL OUTLINE



All Dimensions in Inches (mm).

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